## FEATURES

- Member of the Texas Instruments Widebus ${ }^{\text {TM }}$ Family
- SN74CB3Q Bus Switches Are Equivalent to IDTQS3VH Bus Switches
- 5-V Tolerant I/Os With Device Powered Up or Powered Down
- Low and Flat ON-State Resistance ( $r_{\text {on }}$ ) Characteristics Over Operating Range ( $r_{\text {on }}=5 \Omega$ Typ)
- Rail-to-Rail Switching on Data I/O Ports
- 0- to 5-V Switching With 3.3-V $\mathrm{V}_{\mathrm{cc}}$
- 0- to 3.3-V Switching With $2.5-\mathrm{V} \mathrm{V}_{\mathrm{cc}}$
- B-Port Outputs Are Precharged by Bias Voltage (BIASV) to Minimize Signal Distortion During Live Insertion and Hot Plugging
- Supports PCI Hot Plug
- Bidirectional Data Flow With Near-Zero Propagation Delay
- Low Input/Output Capacitance Minimizes Loading and Signal Distortion ( $\mathrm{C}_{\text {io(OFF) }}=4 \mathrm{pF}$ Typ)
- Fast Switching Frequency ( $\mathrm{f}_{\mathrm{on}}=\mathbf{2 0} \mathbf{~ M H z ~ M a x ) ~}$
- Data and Control Inputs Provide Undershoot Clamp Diodes
- Low Power Consumption ( $\mathrm{I}_{\mathrm{cc}}=0.75 \mathrm{~mA}$ Typ)
- $\mathrm{V}_{\mathrm{cc}}$ Operating Range From 2.3 V to 3.6 V
- Data I/Os Support 0- to 5-V Signaling Levels ( $0.8 \mathrm{~V}, 1.2 \mathrm{~V}, 1.5 \mathrm{~V}, 1.8 \mathrm{~V}, 2.5 \mathrm{~V}, 3.3 \mathrm{~V}, 5 \mathrm{~V}$ )
- Control Inputs Can Be Driven by TTL or 5-V/3.3-V CMOS Outputs
- $I_{\text {off }}$ Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
- 2000-V Human-Body Model (A114-B, Class II)
- 1000-V Charged-Device Model (C101)
- Supports Both Digital and Analog Applications: PCI Hot Plug, Hot Docking, Memory Interleaving, Bus Isolation, and Low-Distortion Signal Gating


## DESCRIPTION/ORDERING INFORMATION

The SN74CB3Q16811 is a high-bandwidth FET bus switch utilizing a charge pump to elevate the gate voltage of the pass transistor, providing a low and flat ON-state resistance ( $\mathrm{r}_{\mathrm{on}}$ ). The low and flat ON -state resistance allows for minimal propagation delay and supports rail-to-rail switching on the data input/output (I/O) ports. The device also features low data I/O capacitance to minimize capacitive loading and signal distortion on the data bus. Specifically designed to support high-bandwidth applications, the SN74CB3Q16811 provides an optimized interface solution ideally suited for broadband communications, networking, and data-intensive computing systems.

ORDERING INFORMATION

| $\mathrm{T}_{\text {A }}$ | PACKAGE ${ }^{(1)}$ |  | ORDERABLE PART NUMBER | TOP-SIDE MARKING |
| :---: | :---: | :---: | :---: | :---: |
| $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$ | SSOP - DL | Tube | SN74CB3Q16811DL | CB3Q16811 |
|  |  | Tape and reel | SN74CB3Q16811DLR |  |
|  | TSSOP - DGG | Tape and reel | SN74CB3Q16811DGGR | CB3Q16811 |
|  | TVSOP - DGV | Tape and reel | SN74CB3Q16811DGVR | BW811 |

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.
DESCRIPTION/ORDERING INFORMATION (CONTINUED)
The SN74CB3Q16811 is organized as two 12 -bit bus switches with separate output-enable ( $1 \overline{\mathrm{OE}}, 2 \overline{\mathrm{OE}}$ ) inputs. It can be used as two 12 -bit bus switches or as one 24 -bit bus switch. When $\overline{O E}$ is low, the associated 12 -bit bus switch is ON , and the A port is connected to the B port, allowing bidirectional data flow between ports. When OE is high, the associated 12-bit bus switch is OFF, and a high-impedance state exists between the A and B ports. The B port is precharged to bias voltage (BIASV) through the equivalent of a $10-\mathrm{k} \Omega$ resistor when $\overline{\mathrm{OE}}$ is high or if the device is powered down $\left(\mathrm{V}_{\mathrm{CC}}=0 \mathrm{~V}\right)$.

## SN74CB3Q16811 <br> 24-BIT SWITCH WITH PRECHARGED OUTPUTS <br> $2.5-\mathrm{V} / 3.3-\mathrm{V}$ LOW-VOLTAGE FET BUS SWITCH

TeXAs

SCDS153B-OCTOBER 2003-REVISED MARCH 2005
During insertion (or removal) of a card into (or from) an active bus, the card's output voltage may be close to GND. When the connector pins make contact, the card's parasitic capacitance tries to force the bus signal to GND, creating a possible glitch on the active bus. This glitching effect can be reduced by using a bus switch with precharged bias voltage (BIASV) of the bus switch equal to the input threshold voltage level of the receivers on the active bus. This method ensures that any glitch produced by insertion (or removal) of the card does not cross the input threshold region of the receivers on the active bus, minimizing the effects of live-insertion noise.
This device is fully specified for partial-power-down applications using $\mathrm{I}_{\text {off }}$. The $\mathrm{I}_{\text {off }}$ circuitry prevents damaging current backflow through the device when it is powered down.
To ensure the high-impedance state during power up or power down, $\overline{O E}$ should be tied to $\mathrm{V}_{\mathrm{CC}}$ through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

DGG, DGV, OR DL PACKAGE
(TOP VIEW)

| BIASV |  | $1 \overline{O E}$ |
| :---: | :---: | :---: |
| 1A1 | 255 | $2 \overline{O E}$ |
| 1A2 | 354 | 1B1 |
| 1 A3 | 453 | 1B2 |
| 1A4 | 552 | 1 B 3 |
| 1A5 | 651 | 1B4 |
| 1A6 | 750 | 1B5 |
| GND | $8 \quad 49$ | GND |
| 1A7 | 948 | $1 \mathrm{B6}$ |
| 1A8 | $10 \quad 47$ | 1B7 |
| 1A9 | $11 \quad 46$ | 1B8 |
| 1A10 | 1245 | 1B9 |
| 1A11 | 1344 | 1B10 |
| 1A12 | $14 \quad 43$ | 1B11 |
| 2A1 | 1542 | 1B12 |
| 2A2 | $16 \quad 41$ | 2B1 |
| $V^{\text {CC }}$ | $17 \quad 40$ | 2B2 |
| 2A3 | 1839 | 2B3 |
| GND | 1938 | GND |
| 2A4 | $20 \quad 37$ | 2B4 |
| 2A5 | $21 \quad 36$ | 2B5 |
| 2A6 | 2235 | 2B6 |
| 2A7 | $23 \quad 34$ | 2B7 |
| 2A8 | 2433 | 2B8 |
| 2A9 | $25 \quad 32$ | 2B9 |
| 2A10 | $26 \quad 31$ | 2B10 |
| 2A11 | $27 \quad 30$ | 2B11 |
| 2A12 [ | $28 \quad 29$ | 2B12 |

Table 1. FUNCTION TABLE
(EACH 12-BIT BUS SWITCH)

| INPUT <br> $\mathbf{O E}$ | INPUT/OUTPUT <br> $\mathbf{A}$ | FUNCTION |
| :---: | :---: | :---: |
| L | B | A port = B port |
| H | Z | Disconnect <br> B port $=$ BIASV |

## LOGIC DIAGRAM (POSITIVE LOGIC)


2.5-V/3.3-V LOW-VOLTAGE FET BUS SWITCH

SCDS153B-OCTOBER 2003-REVISED MARCH 2005
SIMPLIFIED SCHEMATIC, EACH FET SWITCH (SW)

(1) EN is the internal enable signal applied to the switch.

## Absolute Maximum Ratings ${ }^{(1)}$

over operating free-air temperature range (unless otherwise noted)

|  |  |  | MIN | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {CC }}$ | Supply voltage range |  | -0.5 | 4.6 | V |
| BIASV | BIAS supply voltage range |  | -0.5 | 7 | V |
| $\mathrm{V}_{\text {IN }}$ | Control input voltage range ${ }^{(2)(3)}$ |  | -0.5 | 7 | V |
| $\mathrm{V}_{1 / \mathrm{O}}$ | Switch I/O voltage range ${ }^{(2)(3)(4)}$ |  | -0.5 | 7 | V |
| $\mathrm{I}_{\text {K }}$ | Control input clamp current | $\mathrm{V}_{\text {IN }}<0$ |  | -50 | mA |
| $\mathrm{I}_{\text {I/OK }}$ | I/O port clamp current | $\mathrm{V}_{1 / 0}<0$ |  | -50 | mA |
| $\mathrm{I}_{1 / \mathrm{O}}$ | ON-state switch current ${ }^{(5)}$ |  |  | $\pm 64$ | mA |
|  | Continuous current through $\mathrm{V}_{\mathrm{CC}}$ or GND |  |  | $\pm 100$ | mA |
|  |  | DGG package |  | 64 |  |
| $\theta_{\mathrm{JA}}$ | Package thermal impedance ${ }^{(6)}$ | DGV package |  | 48 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  | DL package |  | 56 |  |
| $\mathrm{T}_{\text {stg }}$ | Storage temperature range |  | -65 | 150 | ${ }^{\circ} \mathrm{C}$ |

[^0]Recommended Operating Conditions ${ }^{(1)}$

|  |  |  | MIN | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{C C}$ | Supply voltage |  | 2.3 | 3.6 | V |
| BIASV | Bias voltage |  | 0 | 5 | V |
| $\mathrm{V}_{\mathrm{IH}}$ | High-level control input voltage | $\mathrm{V}_{\mathrm{CC}}=2.3 \mathrm{~V}$ to 2.7 V | 1.7 | 5.5 | V |
|  |  | $\mathrm{V}_{\mathrm{CC}}=2.7 \mathrm{~V}$ to 3.6 V | 2 | 5.5 |  |
| $\mathrm{V}_{\text {IL }}$ | Low-level control input voltage | $\mathrm{V}_{\mathrm{CC}}=2.3 \mathrm{~V}$ to 2.7 V | 0 | 0.7 | V |
|  |  | $\mathrm{V}_{\mathrm{CC}}=2.7 \mathrm{~V}$ to 3.6 V | 0 | 0.8 |  |
| $\mathrm{V}_{\text {I/O }}$ | Data input/output voltage |  | 0 | 5.5 | V |
| $\mathrm{T}_{\text {A }}$ | Operating free-air temperature |  | -40 | 85 | ${ }^{\circ} \mathrm{C}$ |

(1) All unused control inputs of the device must be held at $\mathrm{V}_{\mathrm{CC}}$ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

## Electrical Characteristics ${ }^{(1)}$

over recommended operating free-air temperature range (unless otherwise noted)

| PARAMETER |  | TEST CONDITIONS |  |  | MIN TYP $^{(2)}$ | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{IK}}$ |  | $\mathrm{V}_{C C}=3.6 \mathrm{~V}$, | $\mathrm{I}_{\mathrm{I}}=-18 \mathrm{~mA}$ |  |  | -1.8 | V |
| $\mathrm{I}_{\mathrm{IN}}$ | Control inputs | $\mathrm{V}_{C C}=3.6 \mathrm{~V}$, | $\mathrm{V}_{\text {IN }}=0$ to 5.5 V |  |  | $\pm 1$ | $\mu \mathrm{A}$ |
| $\mathrm{I}_{0}$ | B port | $V_{C C}=3 . \mathrm{V}$, | $\begin{aligned} & \text { BIASV }=2.4 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{O}}=0, \end{aligned}$ | Switch OFF, $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\mathrm{CC}}$ or $\operatorname{GND}$ | 0.2 |  | mA |
| $\mathrm{l}_{\mathrm{Oz}}{ }^{(3)}$ |  | $\mathrm{V}_{\mathrm{CC}}=3.6 \mathrm{~V}$, | $\begin{aligned} & \mathrm{V}_{\mathrm{O}}=0 \text { to } 5.5 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{I}}=0, \end{aligned}$ | Switch OFF, $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}}$ or $G N D$ |  | $\pm 1$ | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\text {off }}$ |  | $\mathrm{V}_{\mathrm{CC}}=0$, | $\mathrm{V}_{\mathrm{O}}=0$ to 5.5 V , | $\mathrm{V}_{1}=0$ |  | 1 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\mathrm{CC}}$ |  | $\mathrm{V}_{C C}=3.6 \mathrm{~V}$, | $I_{1 / O}=0,$ <br> Switch ON or OFF, | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\text {CC }}$ or GND | 1 | 3 | mA |
| $\Delta \mathrm{lCC}^{(4)}$ | Control inputs | $\mathrm{V}_{C C}=3.6 \mathrm{~V}$, | One input at 3 V , | Other inputs at $\mathrm{V}_{\mathrm{CC}}$ or GND |  | 30 | $\mu \mathrm{A}$ |
| $\mathrm{ICCD}^{(5)}$ | Per control input | $\mathrm{V}_{C C}=3.6 \mathrm{~V}$, | $A$ and $B$ ports open Control input switch | at $50 \%$ duty cycle | 0.38 | 0.45 | $\begin{aligned} & \mathrm{mA} / \\ & \mathrm{MHz} \end{aligned}$ |
| $\mathrm{C}_{\text {in }}$ | Control inputs | $\mathrm{V}_{C C}=3.3 \mathrm{~V}$, | $\mathrm{V}_{\mathrm{IN}}=5.5 \mathrm{~V}, 3.3 \mathrm{~V}$, or |  | 3.5 | 5 | pF |
| $\mathrm{C}_{\text {io(OFF) }}$ | A port | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$, | Switch OFF, <br> $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}}$ or GND , | $\mathrm{V}_{\text {I/ }}=5.5 \mathrm{~V}, 3.3 \mathrm{~V}$, or 0 | 4 | 5 | pF |
| $\mathrm{C}_{\mathrm{io}(\mathrm{ON})}$ |  | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$, | Switch ON, $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}}$ or GND, | $\mathrm{V}_{\mathrm{I} / \mathrm{O}}=5.5 \mathrm{~V}$, 3.3 V , or 0 | 10 | 12.5 | pF |
| $\mathrm{ron}^{(6)}$ |  | $\begin{aligned} & \mathrm{V}_{\mathrm{CC}}=2.3 \mathrm{~V}, \\ & T Y P \text { at } V_{\mathrm{CC}}=2.5 \mathrm{~V} \end{aligned}$ | $\mathrm{V}_{1}=0$, | $\mathrm{I}_{0}=30 \mathrm{~mA}$ | 5 | 8 | $\Omega$ |
|  |  |  | $\mathrm{V}_{1}=1.7 \mathrm{~V}$, | $\mathrm{I}_{\mathrm{O}}=-15 \mathrm{~mA}$ | 5 | 9 |  |
|  |  | $\mathrm{V}_{\mathrm{CC}}=3 \mathrm{~V}$ | $\mathrm{V}_{1}=0$, | $\mathrm{I}_{0}=30 \mathrm{~mA}$ | 5 | 6.5 |  |
|  |  |  | $\mathrm{V}_{\mathrm{I}}=2.4 \mathrm{~V}$, | $\mathrm{I}_{\mathrm{O}}=-15 \mathrm{~mA}$ | 5 | 8 |  |

(1) $\mathrm{V}_{\mathbb{I N}}$ and $\mathrm{I}_{\mathbb{N}}$ refer to control inputs. $\mathrm{V}_{\mathrm{I}}, \mathrm{V}_{\mathrm{O}}, \mathrm{I}_{\mathrm{l}}$, and $\mathrm{I}_{0}$ refer to data pins.
(2) All typical values are at $\mathrm{V}_{C C}=3.3 \mathrm{~V}$ (unless otherwise noted), $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$.
(3) For I/O ports, the parameter $\mathrm{I}_{\mathrm{Oz}}$ includes the input leakage current.
(4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than $V_{C C}$ or GND.
(5) This parameter specifies the dynamic power-supply current associated with the operating frequency of a single control input (see Eigure ${ }^{2}$ ).
(6) Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two ( A or B ) terminals.

## Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

| PARAMETER | FROM (INPUT) | FROM (INPUT) | TO (OUTPUT) | $\begin{gathered} \mathrm{V}_{\mathrm{Cc}}=2.5 \mathrm{~V} \\ \pm 0.2 \mathrm{~V} \end{gathered}$ |  | $\begin{gathered} \mathrm{V}_{\mathrm{cc}}=3.3 \mathrm{~V} \\ \pm 0.3 \mathrm{~V} \end{gathered}$ |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | MIN | MAX | MIN | MAX |  |
| $\mathrm{f}_{\text {OE }}{ }^{(1)}$ |  | $\overline{\mathrm{OE}}$ | A or B |  | 10 |  | 20 | MHz |
| $\mathrm{t}_{\mathrm{pd}}{ }^{(2)}$ |  | A or B | B or A |  | 0.09 |  | 0.15 | ns |
| $t_{\text {Pzi }}$ | BIASV = GND | סE | A or B | 1.5 | 8 | 1.5 | 8 | ns |
| $\mathrm{t}_{\text {PZL }}$ | BIASV $=3 \mathrm{~V}$ |  |  | 1.5 | 8 | 1.5 | 8 |  |
| $\mathrm{t}_{\text {PHZ }}$ | BIASV = GND | $\overline{\mathrm{OE}}$ | A or B | 1 | 7.5 | 1 | 7.5 | ns |
| $t_{\text {PLZ }}$ | BIASV $=3 \mathrm{~V}$ |  |  | 1 | 7.5 | 1 | 7.5 |  |

(1) Maximum switching frequency for control input ( $V_{O}>V_{C C}, V_{I}=5 \mathrm{~V}, R_{L} \geq 1 \mathrm{M} \Omega, C_{L}=0$ )
(2) The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).


Figure 1. Typical $r_{\text {on }}$ vs $V_{l}$


Figure 2. Typical $I_{c c}$ vs $\overline{O E}$ Switching Frequency

## PARAMETER MEASUREMENT INFORMATION



| TEST | $\mathrm{V}_{\mathrm{CC}}$ | S1 | $\mathrm{R}_{\mathrm{L}}$ | $\mathrm{V}_{1}$ | $\mathrm{C}_{\mathrm{L}}$ | $\mathrm{V}_{\Delta}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{pd}(\mathrm{s})}$ | $\begin{aligned} & 2.5 \mathrm{~V} \pm 0.2 \mathrm{~V} \\ & 3.3 \mathrm{~V} \pm 0.3 \mathrm{~V} \end{aligned}$ | Open Open | $\begin{aligned} & 500 \Omega \\ & 500 \Omega \end{aligned}$ | $V_{C C}$ or GND <br> $V_{c c}$ or GND | $\begin{aligned} & 30 \mathrm{pF} \\ & 50 \mathrm{pF} \end{aligned}$ |  |
| $\mathbf{t P L z}^{\text {/ }}$ PZL | $\begin{aligned} & 2.5 \mathrm{~V} \pm 0.2 \mathrm{~V} \\ & 3.3 \mathrm{~V} \pm 0.3 \mathrm{~V} \end{aligned}$ | $\begin{aligned} & 2 \times V_{c C} \\ & 2 \times V_{c c} \end{aligned}$ | $\begin{aligned} & 500 \Omega \\ & 500 \Omega \end{aligned}$ | GND GND | $\begin{aligned} & 30 \mathrm{pF} \\ & 50 \mathrm{pF} \end{aligned}$ | $\begin{gathered} 0.15 \mathrm{~V} \\ 0.3 \mathrm{~V} \end{gathered}$ |
| $\mathrm{t}_{\text {PHz }} / \mathrm{tPZH}$ | $\begin{aligned} & 2.5 \mathrm{~V} \pm 0.2 \mathrm{~V} \\ & 3.3 \mathrm{~V} \pm 0.3 \mathrm{~V} \end{aligned}$ | GND GND | $\begin{aligned} & 500 \Omega \\ & 500 \Omega \end{aligned}$ | $\begin{aligned} & \mathrm{v}_{\mathrm{cc}} \\ & \mathrm{v}_{\mathrm{cc}} \end{aligned}$ | $\begin{aligned} & 30 \mathrm{pF} \\ & 50 \mathrm{pF} \end{aligned}$ | $\begin{gathered} 0.15 \mathrm{~V} \\ 0.3 \mathrm{~V} \end{gathered}$ |



NOTES: A. $C_{L}$ includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control.

Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: $\mathrm{PRR} \leq 10 \mathrm{MHz}, \mathrm{Z}_{\mathrm{O}}=50 \Omega, \mathrm{t}_{\mathrm{r}} \leq 2.5 \mathrm{~ns}, \mathrm{t}_{\mathrm{f}} \leq 2.5 \mathrm{~ns}$.
D. The outputs are measured one at a time, with one transition per measurement.
E. $t_{P L Z}$ and $t_{P H Z}$ are the same as $t_{\text {dis }}$.
F. $t_{P Z L}$ and tPZH are the same as ten.
G. $t_{P L H}$ and $t_{P H L}$ are the same as $t_{p d(s)}$. The tpd propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
H. All parameters and waveforms are not applicable to all devices.

Figure 3. Test Circuit and Voltage Waveforms

## PACKAGING INFORMATION

| Orderable Device | Status <br> (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan <br> (2) | Lead finish/ Ball material <br> (6) | MSL Peak Temp <br> (3) | Op Temp ( ${ }^{\circ} \mathrm{C}$ ) | Device Marking <br> (4/5) | Samples |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN74CB3Q16811DGGR | ACTIVE | TSSOP | DGG | 56 | 2000 | RoHS \& Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | CB3Q16811 | Samples |
| SN74CB3Q16811DGVR | ACTIVE | TVSOP | DGV | 56 | 2000 | RoHS \& Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BW811 | Samples |

${ }^{(1)}$ The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.
${ }^{(2)}$ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed $0.1 \%$ by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as " Pb -Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the $<=1000 \mathrm{ppm}$ threshold requirement.
${ }^{(3)}$ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
${ }^{(4)}$ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
${ }^{(5)}$ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a " $\sim$ " will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
${ }^{(6)}$ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents Tl's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall Tl's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

## TAPE AND REEL INFORMATION


*All dimensions are nominal

| Device | Package <br> Type | Package <br> Drawing | Pins | SPQ | Reel <br> Diameter <br> $(\mathbf{m m})$ | Reel <br> Width <br> W1 $(\mathbf{m m})$ | A0 <br> $(\mathbf{m m})$ | B0 <br> $(\mathbf{m m})$ | K0 <br> $(\mathbf{m m})$ | P1 <br> $(\mathbf{m m})$ | W <br> $(\mathbf{m m})$ | Pin1 <br> Quadrant |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN74CB3Q16811DGGR | TSSOP | DGG | 56 | 2000 | 330.0 | 24.4 | 8.6 | 15.6 | 1.8 | 12.0 | 24.0 | Q1 |
| SN74CB3Q16811DGVR | TVSOP | DGV | 56 | 2000 | 330.0 | 24.4 | 6.8 | 11.7 | 1.6 | 12.0 | 24.0 | Q1 |


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN74CB3Q16811DGGR | TSSOP | DGG | 56 | 2000 | 367.0 | 367.0 | 45.0 |
| SN74CB3Q16811DGVR | TVSOP | DGV | 56 | 2000 | 367.0 | 367.0 | 45.0 |



| PIM ** | $\mathbf{1 4}$ | $\mathbf{1 6}$ | $\mathbf{2 0}$ | $\mathbf{2 4}$ | $\mathbf{3 8}$ | $\mathbf{4 8}$ | $\mathbf{5 6}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| A MAX | 3,70 | 3,70 | 5,10 | 5,10 | 7,90 | 9,80 | 11,40 |
| A MIN | 3,50 | 3,50 | 4,90 | 4,90 | 7,70 | 9,60 | 11,20 |

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
D. Falls within JEDEC: $24 / 48$ Pins - MO-153

14/16/20/56 Pins - MO-194


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-194.


NOTES: (continued)
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.


SOLDER PASTE EXAMPLE BASED ON 0.125 mm THICK STENCIL

SCALE: 8 X

NOTES: (continued)
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

DL (R-PDSO-G56)


NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed $0.006(0,15)$.
D. Falls within JEDEC MO-118


## NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-153.


NOTES: (continued)
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.


SOLDER PASTE EXAMPLE BASED ON 0.125 mm THICK STENCIL SCALE:6X

NOTES: (continued)
7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

## IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.
These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. Tl grants you permission to use these resources only for development of an application that uses the Tl products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify Tl and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.
Tl's products are provided subject to Tl's Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. Tl's provision of these resources does not expand or otherwise alter Tl's applicable warranties or warranty disclaimers for TI products.


[^0]:    (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
    (2) All voltages are with respect to ground, unless otherwise specified.
    (3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
    (4) $V_{I}$ and $V_{O}$ are used to denote specific conditions for $V_{I / O}$.
    (5) $I_{l}$ and $I_{0}$ are used to denote specific conditions for $I_{/ / O}$.
    (6) The package thermal impedance is calculated in accordance with JESD 51-7.

